P-Channel 80-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

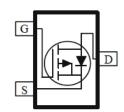
Typical	Appl	icatio	ns:
<i>3</i> I			

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-80	800 @ V _{GS} = -10V	-1.1		
	900 @ V _{GS} = -4.5V	-1.0		







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter			Symbol	Limit	Units
Drain-Source Voltage			V_{DS}	-80	V
Gate-Source Voltage		V_{GS}	±20	V	
04:		T _A =25°C	1	-1.1	
Continuous Drain Current ^a		T _A =70°C	I _D	-0.9	Α
Pulsed Drain Current ^b		I _{DM}	-5		
Continuous Source Current (Diode Conduction) a			Is	-1.6	Α
Davier Discipation a		T _A =25°C	P _D	1.3	W
Power Dissipation ^a	_	T _A =70°C	0.8		V V
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W		
IMAXIIIIUIII JUIICUOII-to-Alfibierit	Steady State	I V OJA	166	C/VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

MI2381P

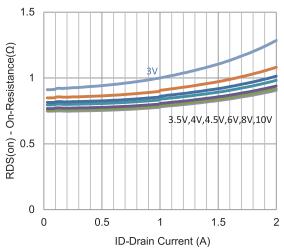
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = -64 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zero Gate Voltage Drain Current	DSS	$V_{DS} = -64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	
On-State Drain Current	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-2			Α
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -1.1 \text{ A}$			800	mΩ
Dialii-Source Oil-Resistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.9 \text{ A}$			900	
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -1.1 \text{ A}$		5		S
Diode Forward Voltage	V_{SD}	$I_{S} = -0.8 \text{ A}, V_{GS} = 0 \text{ V}$		-0.85		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = -40 \text{ V}, V_{GS} = -4.5 \text{ V},$		4		
Gate-Source Charge	Q_{gs}	$V_{DS} = -40 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -1.1 \text{ A}$		1.0		nC
Gate-Drain Charge	Q_{gd}	ID = -1.1 A		1.8		1
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -40 \text{ V}, R_{L} = 36.4 \Omega,$		6		
Rise Time	t _r	$I_{DS} = -40 \text{ V}, K_L = 30.4 \Omega,$ $I_D = -1.1 \text{ A},$		5		no
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		21		ns
Fall Time	t _f	V GEN 10 V, 1 (GEN - 0 12		7		
Input Capacitance	C _{iss}			307		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		24		pF
Reverse Transfer Capacitance	C _{rss}			19		

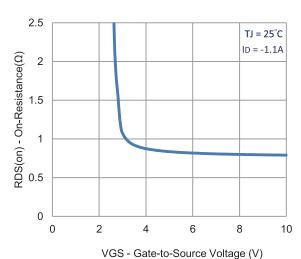
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

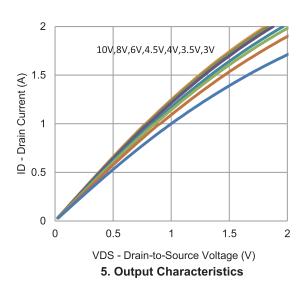
Typical Electrical Characteristics

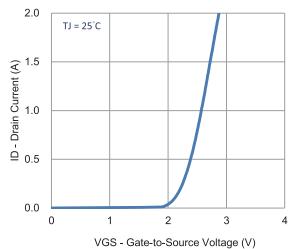


1. On-Resistance vs. Drain Current

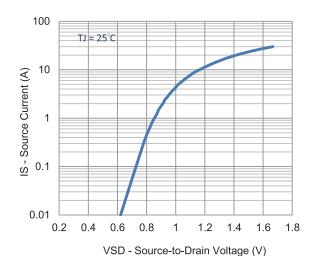


3. On-Resistance vs. Gate-to-Source Voltage

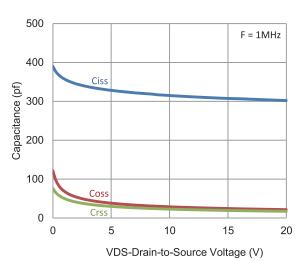




2. Transfer Characteristics

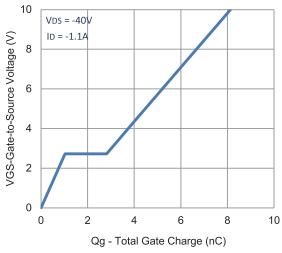


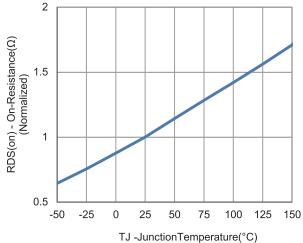
4. Drain-to-Source Forward Voltage



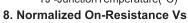
6. Capacitance

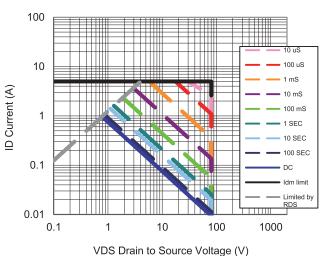


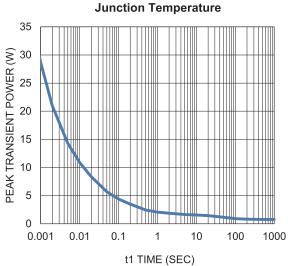




7. Gate Charge

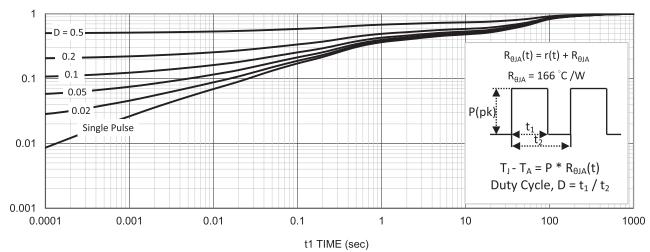






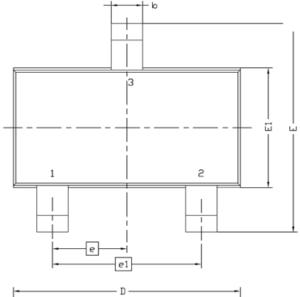
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

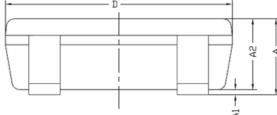


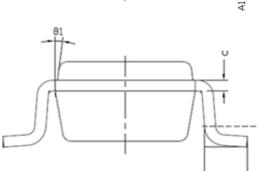
11. Normalized Thermal Transient Junction to Ambient

Package Information

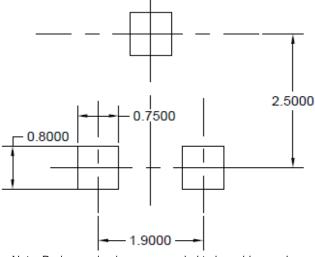


Symbol	MILLIMETERS			
Syllibol	MIN	MAX		
Α	0.8	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1	0.2		
D	2.7	3.1		
Е	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
L	0.3	0.6		
θ1	7° NOM			





Recommended Pad Layout



Note: Drain opening is recommended to be solder mask defined in a copper fill for improved thermal performance

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